

**Amendments to the Claims:**

The following claims will replace all prior versions of the claims in this application (in the unlikely event that no claims follow herein, the previously pending claims will remain):

1. (Currently Amended) A semiconductor laser, comprising:
  - a substrate etched into a mesa structure;
  - an active layer formed directly on the mesa structure and being a core of a waveguide;
  - a first clad layer formed on the active layer;
  - a current blocking layer formed on the etched substrate in both sides of the mesa structure;
  - an etch-stop layer formed on the first clad layer and the current blocking layer;
  - a second clad layer formed on the etch-stop layer being located on an upper portion of the mesa structure, with a predetermined width;
  - an ohmic contact layer formed on the second clad layer;
  - a first electrode contacted with the ohmic contact layer; and
  - a second electrode formed on a bottom side of the substrate.
2. (Original) A semiconductor laser as claimed in Claim 1, wherein the current blocking layer may be formed by a first p type, an n type, and a second p type semiconductor layers,
  - wherein the second p type semiconductor layer is formed with a thickness thinner than that of the first p type semiconductor layer.
3. (Original) The semiconductor laser as claimed in Claim 2, wherein the second p type semiconductor layer is formed with a thickness of 0.2  $\mu\text{m}$  or less.
4. (Original) The semiconductor laser as claimed in Claim 1, wherein the second clad layer may be a p type semiconductor layer.
5. (Original) The semiconductor laser as claimed in Claim 1, further comprising a layer for planarization in both sides of the second clad layer and the ohmic contact layer.
- 6-9. (Cancelled)

10. (Previously Presented) A semiconductor laser, comprising:  
a substrate etched into a mesa structure;  
an active layer formed on the mesa structure and being a core of a waveguide;  
a first clad layer formed on the active layer;  
a current blocking layer formed on the etched substrate in both sides of the mesa structure;  
an etch-stop layer formed on the first clad layer and the current blocking layer;  
a second clad layer formed on the etch-stop layer being located on an upper portion of the mesa structure, with a predetermined width;  
an ohmic contact layer formed on the second clad layer;  
a first electrode contacted with the ohmic contact layer; and  
a second electrode formed on a bottom side of the substrate;  
wherein the current blocking layer may be formed by a first p type, an n type, and a second p type semiconductor layers, and  
wherein the second p type semiconductor layer is formed with a thickness thinner than that of the first p type semiconductor layer.

11. (Cancelled)

12. (Previously Presented) The semiconductor laser as claimed in Claim 10, wherein the second clad layer may be a p type semiconductor layer.

13. (Previously Presented) The semiconductor laser as claimed in Claim 10, further comprising a layer for planarization in both sides of the second clad layer and the ohmic contact layer.

14. (Previously Presented) A semiconductor laser, comprising:  
a substrate etched into a mesa structure;  
an active layer formed on the mesa structure and being a core of a waveguide;  
a first clad layer formed on the active layer;  
a current blocking layer formed on the etched substrate in both sides of the mesa structure;

an etch-stop layer formed on the first clad layer and the current blocking layer;  
a second clad layer formed on the etch-stop layer being located on an upper portion of the mesa structure, with a predetermined width;  
an ohmic contact layer formed on the second clad layer;  
a first electrode contacted with the ohmic contact layer; and  
a second electrode formed on a bottom side of the substrate;  
wherein the current blocking layer may be formed by a first p type, an n type, and a second p type semiconductor layers;  
wherein the second p type semiconductor layer is formed with a thickness thinner than that of the first p type semiconductor layer; and  
wherein the second p type semiconductor layer is formed with a thickness of 0.2  $\mu\text{m}$  or less.

15. (Previously Presented) The semiconductor laser as claimed in Claim 14, wherein the second clad layer may be a p type semiconductor layer.

16. (Previously Presented) The semiconductor laser as claimed in Claim 14, further comprising a layer for planarization in both sides of the second clad layer and the ohmic contact layer.